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Table of Contents

Product Reliability I

Session Co-Chairs: Bob Knoell and Dimitar Dimitrov

Reliability Degradation of High Density DRAM Cell Transistor Junction Leakage Current Induced by Band-to-defect Tunneling Under the Off-state Bias-temperature Stress
Y.P. Kim, Y.W. Park, J.T. Moon, and S.U. Kim 1

A New Method for Predicting Distribution of DRAM Retention Time
Y. Mori, R. Yamada, S. Kamohara, M. Moniwa, K. Ohyu, and T. Yamanaka 7

Is Product Screen Enough to Guarantee Low Failure Rate for the Customer?
M.W. Ruprecht, G. La Rosa, and R.G. Filippi 12

Analysis of Erratic Bits in FLASH Memories
A. Chimenton, P. Pellati, and P. Olivo 17

Individual Cell Measuring Method for FeRAM Retention Testing
N. Tanabe, H. Koike, T. Miwa, J. Yamada, A. Seike, N. Kasai, H. Toyoshima, and H. Hada 23

Yield Enhancement and Yield Management of Silicon Foundries using Iddq "Stress Current Signature"
M. Rubin, D. Leary, and S. Natan 28

Applying Dynamic Voltage Stressing to Reduce Early Failure Rate
C.-Y. Tsao, R.Y. Shiue, C.C. Ting, Y.S. Huang, Y.C. Lin, and J.T. Yue 37

Process & Reliability Interactions

Session Co-Chairs: Fred Kuper and Walter Riordan

A Study of Formation and Failure Mechanism of CMP Scratch Induced Defects on ILD in a W-damascene interconnect SRAM Cell
S.-M. Jung, J.S. Uom, W.S. Cho, Y.J. Bae, Y.-K. Chung, K.S. Yu, K.Y. Kim, and K.T. Kim 42

The Effects of STI Process Parameters on the Integrity of Dual Gate Oxides
H. Lim, S.-J. Lee, J.-M. Youn, T.-H. Ha, J.-H. Lim, B.-H. Choi, K.-J. Kim, H.-J. Kim, K.-T. Kim, and H.-G. Byun 48

Improvement in Retention Reliability of SONOS Nonvolatile Memory Devices by Two-step High Temperature Deuterium Anneals
J. Bu and M.H. White, ... 52

Data Retention Failure in NOR Flash Memory Cells
W.H. Lee, D.-K. Lee, Y.-M. Park, K.-S. Kim, K.-O. Ahn, and K.-D. Suh 57

A New Conduction Mechanism for the Anomalous Cells in Thin Oxides Flash EEPROMs
A. Modelli, F. Gilardoni, D. Ielmini, and A.S. Spinelli 61

N-Channel Versus P-Channel Flash EEPROM-Which One has Better Reliabilities
S.S. Chung, S.T. Liaw, C.M. Yih, Z.H. Ho, C.J. Lin, D.S. Kuo, and M.S. Liang 67

New Technique for Fast Characterization of SILC Distribution in Flash Arrays
D. Ielmini, A.S. Spinelli, A.L. Lacaita, L. Confalonieri, and A. Visconti 73

MEMS Reliability Characterization

Session Co-Chairs: Danelle Tanner and Susanne Arney

Reliability of a MEMS Torsional Ratcheting Actuator
D.M. Tanner, J.A Walraven, S.M. Barnes, N.F. Smith, F. Bitsie, and S.E. Swanson 81

Full Three-Dimensional Motion Characterization of a Gimballed Electrostatic Microactuator
C. Rembe, L. Muller, R.S. Muller, and R.T. Howe 91

Non-Destructive Resonant Frequency Measurement on MEMS Actuators
N.F. Smith, D.M. Tanner, S.E. Swanson and S.L. Miller 99

Size Effect on the Mechanical Properties and Reliability Analysis of Microfabricated Polysilicon Thin Films
J.N. Ding, Y.G. Meng, and S.Z. Wen 106

Packaging and Assembly

Session Co-Chairs: Tom Moore and S. Sidharth

(invited, ESREF best paper) A Simple Model for the Mode I Popcorn Effect for IC Packages
P. Alpern, K.C. Lee, R. Dudek, and R. Tigner

published in Microelectronics Reliability, Special Issue:
Proc. 11th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF 2000), pp 1503

Improving Corrosion-Resistance of Silicon-Glass Micropackages Using Boron Doping and/or Self-Induced Galvanic Bias
B.H. Stark, M.R. Dokmeci, T.J. Harpster, and K. Najafi 112

A Fatigue Theory for Solders
S. Wen and L.M. Keer 120

The Concept of Relative Damage Stress and its Application to Electronic Packaging Solder Joint Reliability
X. Ma, Y. Qian, and X. Zhang 128

Oxide I

Session Co-Chairs: Robin Degraeve and Paul Nicollian

(Invited) Physical and Predictive Models of Ultra Thin Oxide Reliability in CMOS Devices and Circuits
J.H. Stathis 132

(Invited) Direct Experimental Evidence Linking Silicon Dangling Bond Defects to Oxide Leakage Currents
P.M. Lenahan, J.J Mele, J.P. Campbell, A. Y. Kang, R.K. Lowry, D. Woodbury, S.T. Liu, and R. Weimer 150

Nanoscale Observations of the Electrical Conduction of Ultra Thin SiO_2 Films with Conducting Atomic Force Microscopy
M. Porti, M. Nafría, X. Aymerich, A. Olbrich and B. Ebersberger 156

Softening of Breakdown in Ultra-thin Gate Oxide nMOSFETs at Low Inversion Layer Density
S. Lombardo, F. Crupi, and J.H. Stathis 163

Calculating the Error in Long Term Oxide Reliability Estimates
B.P. Linder, J.H. Stathis, and D.J. Frank 168

WLR for Interconnects

Session Co-Chairs: J. Joseph Clement and Armin Fischer

Comparison of Isothermal, Constant Current and SWEAT Wafer Level EM Testing Methods
T.C. Lee, D. Tibel, T.D. Sullivan, and S. Forhan 172

Real Case Study For Isothermal EM Test As A Process Control Methodology
S.-Y. Lee, J.B. Lai, S.C. Lee, L.H. Chu, Y. S. Huang, R.Y. Shiue, Y.K. Peng and J.T. Yue, ... 184

Experimental Comparison of Wafer Level Reliability (WLR) and Packaged Electromigration Tests
C. Ryu, T.-L. Tsai, A. Rogers, C. Jesse, T. Brozek, D. Zarr, M. Adamson, S. Nayak, and J.A. Walls 189

Comparison of Via/Line Package Level vs. Wafer Level Results
D. Tibel and T.D. Sullivan 194

Optoelectronics and Compound Semiconductor

Session Co-Chairs: Sammy Kayali and J.J. Liou

Accelerated Stressing and Degradation Mechanisms for Si-based Photo-emitters
A. Chatterjee, A. Verma, B.L. Bhuva, E. D. Jansen, and W.-C. Lin 200

Low-Temperature, High-Current Lifetests on InP-Based HBT's
B.M. Paine, S. Thomas III, and M.J. Delaney 206

Degradation Characteristics of AlGaN/GaN High Electron Mobility Transistors
H. Kim, V. Tilak, B.M. Green, H. Cha, J.A. Smart, J.R. Shealy, and L.F. Eastman 214

ESD/LATCHUP

Session Co-Chairs: Robert Gauthier and Jeremy Smith

Characterization And Investigation Of The Interaction Between Hot Electron and Electrostatic Discharge Stresses Using NMOS Devices in 0.13 μm CMOS Technology
A. Salman, R. Gauthier, W. Stadler, K. Esmark, M. Muhammad, C. Putnam, and D. Ioannou 219

Non-uniform Bipolar Conduction in Single Finger NMOS Transistors and Implications for Deep Submicron ESD Design
K.-H. Oh, C. Duvvury, C. Salling, K. Banerjee, and R.W. Dutton 226

Advanced 2D Latch-up Device Simulation-a Powerful Tool During Development in the Pre-silicon Phase
S. Bargstädt-Franke and K. Oettinger 235

An Analysis of Bipolar Breakdown and its Application to the Design of ESD Protection Circuits
S. Joshi, R. Ida, P. Givelin, and E. Rosenbaum 240

Parasitic Bipolar Transistor Model using Generated-Hole-Dependent Base Resistance
K. Suzuki, H. Anzai, T. Nomura, and S. Satoh 246

Design and Analysis of New Protection Structures for Smart Power Technology with Controlled Trigger and Holding Voltage
V. De Heyn, G. Groeseneken, B. Keppens, M. Natarajan, L. Vacaresse, and G. Gallopyn 253

PRODUCT RELIABILITY II

Session Co-Chairs: Rich Blish and Courtney Black

Historical Trend in Alpha-Particle induced Soft Error Rates of the Alpha Microprocessor
N. Seifert, D. Moyer, N. Leland, and R. Hokinson 259

A Reliability Methodology for Low Temperature Data Retention in Floating Gate Non-Volatile Memories
P.J. Kuhn, A. Hoefler, T.S. Harp, B.E. Homung, R.E. Paulsen, D. Burnett, and J.M. Higman 266

High-Performance Chip Reliability from Short-Time-Tests: Statistical Models for Optical Interconnect and HCI/TDDB/NBTI Deep-Submicron Transistor Failures
A. Haggag, W. McMahon, K. Hess, K. Cheng, J. Lee, and J. Lyding 271

An Application-Specific Usage Model for Flash Memory Read Disturb Reliability
T.S. Harp, P.J. Kuhn, J.M. Higman, R.E. Paulsen, and B.E. Hornung 280

FAILURE ANALYSIS

Session Co-Chairs: Jacob Phang and Travis Eiles

Case History: Novel FA Techniques Used to Recover EEPROM Data from the Swissair 111 Crash
R. Haythornthwaite, A. Earle, A. Rahal, and D. James 283

Novel Nondestructive and Non-electrical-contact Failure Analysis Technique - Laser-SQUID Microscopy
K. Nikawa and S. Inoue 289

Analysis of Via-Void Generation Mechanism for Giga-bit-scale DRAM
D.H. Kim, J.-S. Park, B.C. Kim, S.-C. Lee, M.-K. Bae, J.W. Nam, I.S. Park, H.Y. Kim, T.-K. Kim, D.W. Choi, J.Y. Lee, J.-S. Kim, Y.-J. Park, J.-I. Hong, and J.-W. Park 294

Study of Metal Impurities Behavior due to Difference in Isolation Structure on ULSI Devices
K. Matsukawa, Y. Kimura, H. Yamamoto, and Y. Mashiko 299

High SRAM Standby Current Due to the Printing of Spurious Images
S.-Y. Tang, M. Mims, T. Cynkar, P.J. Marcoux, and D.H. Eaton 303

Process Induced Damage

Session Co-Chairs: Terence Hook and Kin P. Cheung

The Impact of Trench Geometry and Processing on the Performance and Reliability of Low Voltage Power UMOSFETs
S.A. Suliman, N. Gallogunta, L. Trabzon, J. Hao, G. Dolny, R. Ridley T. Grebs, J. Benjamin, C. Kocon, J. Zeng, C.M. Knoedler, M. Horn, O.O. Awadelkarim, S.J. Fonash, and J. Ruzyllo 308

The Effects of Plasma Induced Damage on Transistor Degradation and the Relationship to Field Programmable Gate Array Performance
F.E. Pagaduan, J.K. Lee, V. Vedagarbha, K. Lui, M.J. Hart, D. Gitlin, T. Takaso, S. Kamiyama, and K. Nakayama 315

Improvement of MOSFET Subthreshold Leakage Current by its Irradiation with Hydrogen Radicals Generated in Microwave-Excited High-Density Inert Gas Plasma
Y. Saito, H. Takahashi, K. Ohtsubo, M. Hirayama, S. Sugawa, H. Aharoni, and T. Ohmi 319

Interconnect Reliability

Session Co-Chairs: Timothy Sullivan and James Walls

Reservoir Modeling for Electromigration Improvement of Metal Systems with Refractory Barriers
M.J. Dion 327

The Quantitative Assessment of Stress-induced Voiding in Process Qualification
A.H. Fischer and A.E. Zitzelsberger 334

Statistics of Electromigration Early Failures in Cu/oxide Dual-damascene Interconnects
E.T. Ogawa, K.-D. Lee, H. Matsuhashi, K.-S. Ko, P.R. Justison, A.N. Ramamurthi, A.J. Bierwag, P.S. Ho, V.A. Blaschke, and R.H. Havemann 341

Trade-off Between Reliability and Post-CMP Defects with Recrystallization Anneal in Copper Damascene Interconnects
G.B. Alers, D. Dornisch, J. Siri, K. Kattige, L. Tam, E. Broadbent, and G.W. Ray 350

Impact of Low-K Dielectrics and Barrier Metals on TDDB Lifetime of Cu Interconnects
J. Noguchi, T. Saitoh, N. Ohashi, H. Ashihara, H. Maruyama, M. Kubo, H. Yamaguchi, D. Ryuzaki, K.I. Takeda, and K. Hinode 355

Oxide II

Session Co-Chairs: Paul Nicollian and Robin Degraeve

Relation Between Breakdown Mode and Breakdown Location in Short Channel NMOSFETs and its Impact on Reliability Specifications
R. Degraeve, B. Kaczer, A. De Keersgieter, and G. Groeseneken 360

Analytic Modeling of Leakage Current Through Multiple Breakdown Paths in SiO_2 Films
E. Miranda, and J. Suñé 367

Experimental Study of Gate Voltage Scaling for TDDB under Direct Tunneling Regime
M. Takayanagi, S. Takagi, and Y. Toyoshima 380

Accurate and Robust Noise-based Trigger Algorithm for Soft Breakdown Detection in Ultra Thin Oxides
P. Roussel, R. Degraeve, G. Van den bosch, B. Kaczer, and G. Groeseneken 386

Soft Breakdown Triggers for Large Area Capacitors Under Constant Voltage Stress
J. Schmitz, H.J. Kretschmann, H.P. Tuinhout, and P.H. Woerlee 393

Hot Carriers

Session Co-Chairs: Giuseppe La Rosa and Roland Thewes

Role of E-E Scattering in the Enhancement of Channel Hot Carrier Degradation of Deep Sub-Micron NMOSFETs at high V_{GS} Conditions
S.E. Rauch III, G. La Rosa, and F.J. Guarin 399

Analysis of New Hot Carrier Degradation Phenomena: "W" or "S" Shape Evolution of LDD NMOSFET
J.-R. Shih, L.H. Chu, J.H. Lee, R.Y. Shiue, Y.K.. Peng, and J.T. Yue 406

On the Dominant Interface Trap Generation Process During Hot-Carrier Stressing
D.S. Ang and C.H. Ling, ... 412

A New Physical and Quantitative Width Dependent Hot Carrier Model for Shallow-Trench-Isolated CMOS Devices
S.S. Chung, S.-J. Chen, W.-J. Yang, and J.-J. Yang 419

Hot-Carrier Reliability of P-MOSFET with Ultra-Thin Silicon Nitride Gate Dielectric
I. Polishchuk, Y.-C. Yeo, Q. Lu, T.-J. King, and C. Hu 425

Biographies 431

Index to Session Paper # 452

2001 Committees 453

1999 Paper Awards 457

2001 Tutorial Program 459

2001 Equipment Demonstrations 462

65